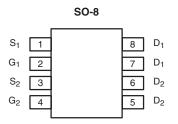


# 4961GM-VB Datasheet Dual P-Channel 20V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)			
	0.018 at V <sub>GS</sub> = - 4.5 V	- 8.9			
- 20	0.022 at V <sub>GS</sub> = - 2.5 V	- 8.1			
	0.030 at V <sub>GS</sub> = - 1.8 V	- 3.6			



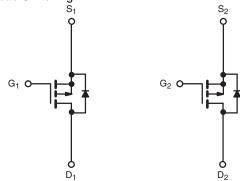
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- Advanced High Cell Density Process
- Compliant to RoHS Directive 2002/95/EC

# Pb-free ROHS COMPLIANT HALOGEN FREE Analysis

#### **APPLICATIONS**

Load Switching



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	<sub>A</sub> = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 20		V
Gate-Source Voltage		V <sub>GS</sub>	± 12		
Continuous Dunis Comment /T 450 9008	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 8.9	- 6.7	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 7.1	- 5.4	
Pulsed Drain Current		I <sub>DM</sub>	- 30		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 1.7	- 0.9	
W	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.0	1.1	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	] ' <sup>*</sup> D	1.3	0.7	"
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestore bounding to Aughing 18	t ≤ 10 s	$R_{thJA}$	46	62.5	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	□thJA	80	110	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	24	32	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



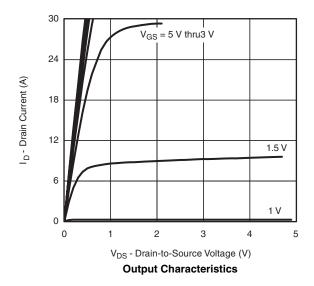
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -350 \mu A$	- 0.4		- 1.0	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zava Cata Valtaga Dvain Cuwant	1	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V - 30			Α
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 8.9 A		0.018		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 8.1 A	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 8.1 A			Ω
		V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 3.6 A		0.030		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 8.9 A		26		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 1.7 A, V <sub>GS</sub> = 0 V		- 0.7	- 1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$			34.5	52	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -8.9 \text{ A}$		5.1		nC
Gate-Drain Charge	$Q_{gd}$	1		9.6		
Gate Resistance	$R_g$			9		Ω
Turn-On Delay Time	t <sub>d(on)</sub>			25	40	
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 10 V, $R_L$ = 6 $\Omega$		46	70	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$		230	345	ns
Fall Time	t <sub>f</sub>			155	235	1
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 1.7 A, dl/dt = 100 A/μs		128	200	

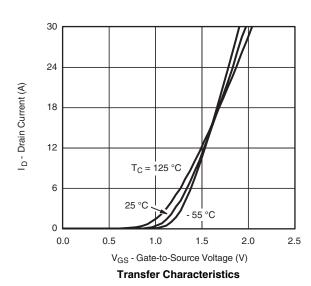
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

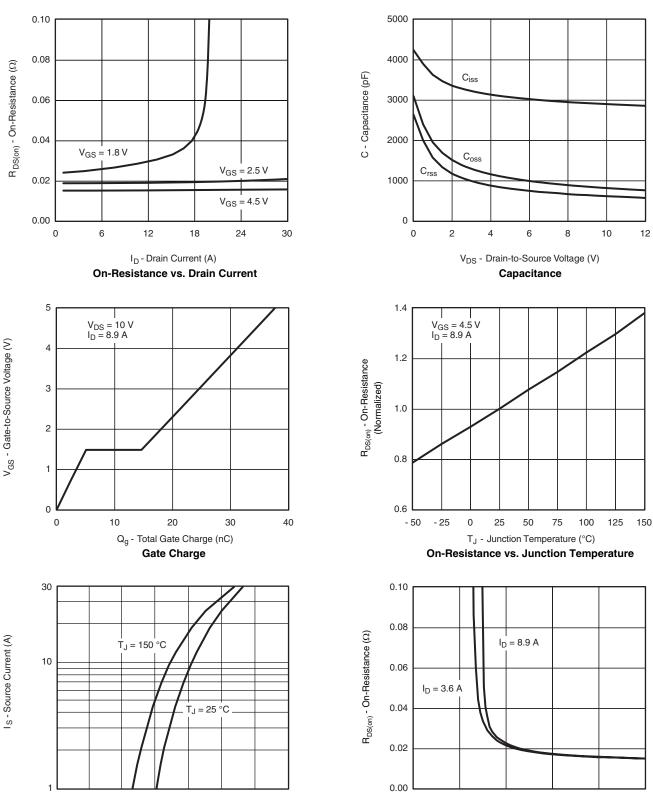
#### TYPICAL CHARACTERISTICS 25 °C unless otherwise noted







#### TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



0

0.0

0.2

0.4

0.6

0.8

V<sub>SD</sub> - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

1.0

1.2

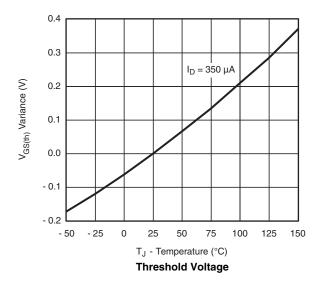
5

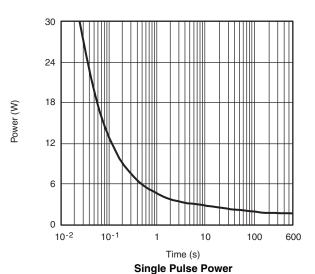
 $V_{GS}$  - Gate-to-Source Voltage (V)

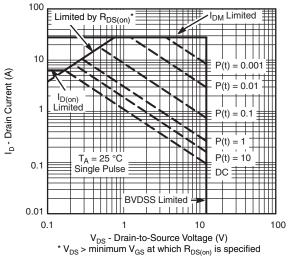
On-Resistance vs. Gate-to-Source Voltage



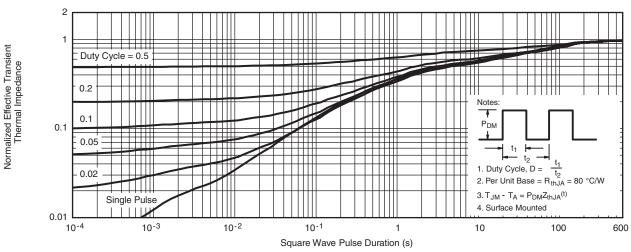
#### TYPICAL CHARACTERISTICS 25 °C unless otherwise noted







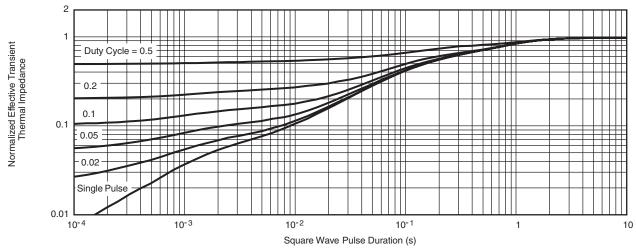




Normalized Thermal Transient Impedance, Junction-to-Ambient



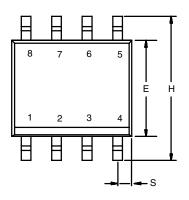
#### TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



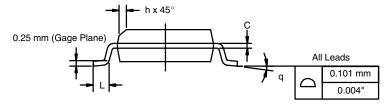
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	INCHES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. J. 11-Sep-06						

DWG: 5498



#### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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